

MMBT5087

PNP EPITAXIAL SILICON TRANSISTOR

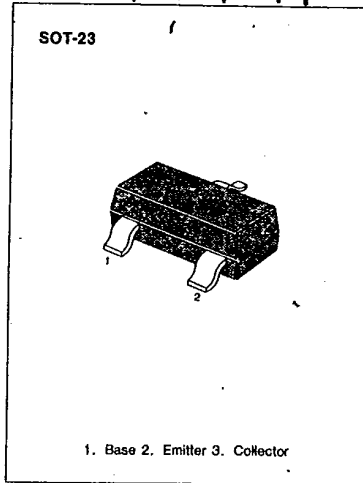
T-29-19

LOW NOISE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	3	V
Collector Current	I _C	50	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT5086 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _C = 100µA, I _E = 0	50		V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = 1.0mA, I _B = 0	50		V
Collector Cutoff Current	I _{CB0}	V _{CB} = 35V, I _E = 0		50	nA
DC Current Gain	h _{FE}	V _{CE} = 5V, I _C = 1.0mA	250	800	
		V _{CE} = 5V, I _C = 1.0mA	250		
		V _{CE} = 5V, I _C = 1.0mA	250		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 1.0mA, I _B = 1.0mA		0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = 1.0mA, I _B = 1.0mA		0.85	V
Current Gain-Bandwidth Product	f _T	I _C = 500µA, V _{CE} = 5V f = 20MHz	40		MHz
Output Capacitance	C _{ob}	V _{CB} = 5V, I _E = 0 f = 100kHz		4.0	pF
Noise Figure	NF	V _{CE} = 5V, I _C = 20mA R _S = 10KΩ f = 10Hz to 15.7KHz		2	dB
		V _{CE} = 5V, I _C = 100µA R _S = 3KΩ, f = 1KHz		2	dB

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Marking

